

**Silicon NPN transistor epitaxial type (darlington)
D5943**

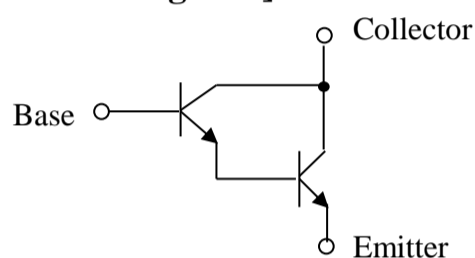
[Applications]

Motor driver

[Feature]

Darlington connection for a high hFE hFE=18k(min.) at VCE= 5V, IC= 100mA
High input impedance

[Circuit diagram]



[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	40	V
Collector-emitter voltage	VCEO	30	V
Emitter-base voltage	VEBO	10	V
Collector current	IC	300	mA
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	40	-	-	V	IC= 100uA
Collector-emitter breakdown voltage	BVCEO	30	-	-	V	IC= 1mA
Emitter-base breakdown voltage	BVEBO	10	-	-	V	IE= 100uA
Collector cut-off current	ICBO	-	-	100	nA	VCB= 30V
Emitter cut-off current	IEBO	-	-	100	nA	VEB= 10V
DC current gain 1	hFE 1	4k	-	-	-	VCE= 5V, IC= 1mA
DC current gain 2	hFE 2	10k	-	-	-	VCE= 5V, IC= 10mA
DC current gain 3	hFE 3	18k	-	-	-	VCE= 5V, IC= 100mA
Collector-emitter saturation voltage	VCE(sat)	-	-	1	V	IC= 100mA, IB= 100uA
Transition frequency	fT	-	200	-	MHz	VCE= 5V, IE= -10mA
Collector output capacitance	Cob	-	2	-	pF	VCB= 30V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

Fig.1 VBE(on) - IC
at VCE= 5V, Ta= 25C

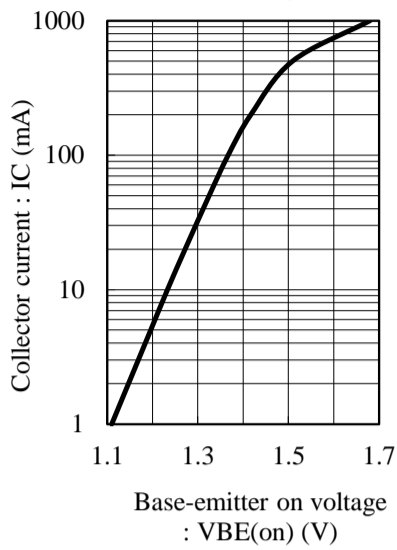


Fig.2 hFE - IC
at VCE= 5V, Ta= 25C

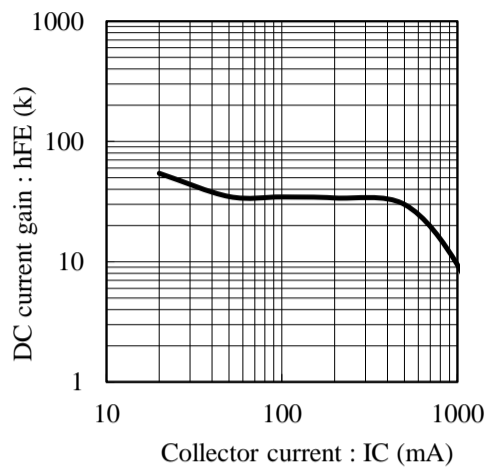


Fig.3 VCE(sat) - IC
at IC/IB= 1000, Ta= 25C

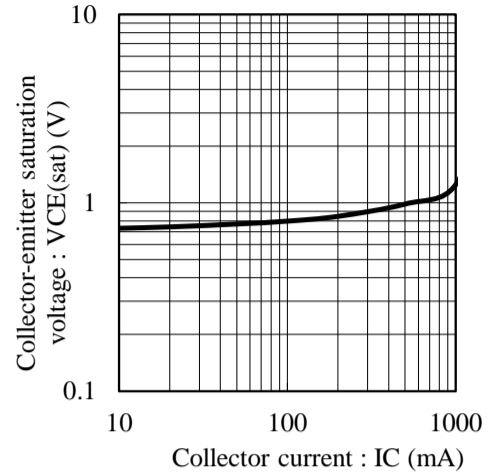


Fig.4 VBE(sat) - IC
at IC/IB= 1000, Ta= 25C

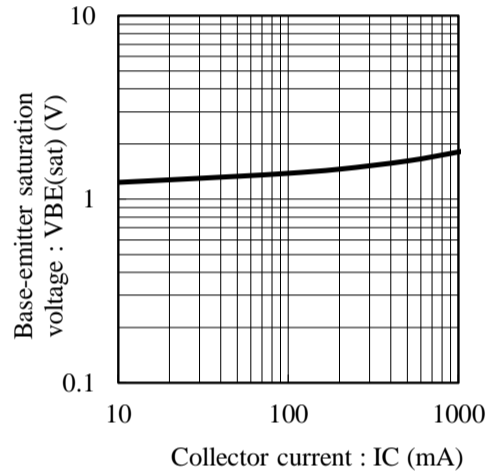


Fig.5 fT - IE
at VCE= 5V, Ta= 25C

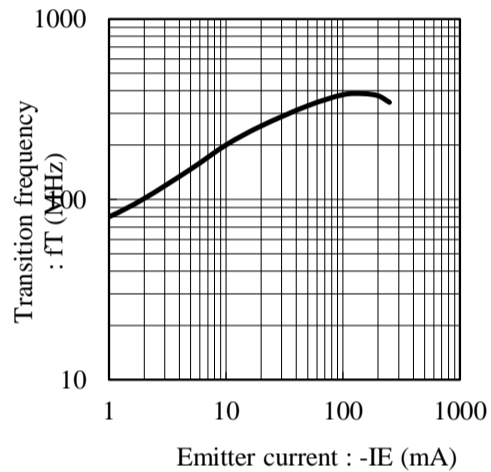


Fig.6 Cob - VCB
at f= 1MHz, Ta= 25C

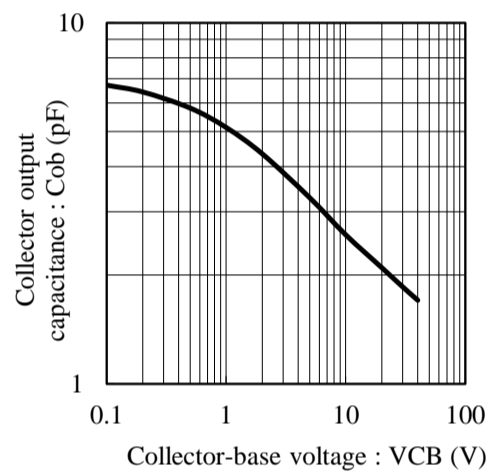


Fig.7 Cib - VEB
at f= 1MHz, Ta= 25C

